

Kritika Aditya

List of Publications by Year in descending order

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12
papers

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1478505

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12
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117
citing authors

#	ARTICLE	IF	CITATIONS
1	Superior Transient Response to Heavy-Ion Irradiation by N-Channel SOI-FinFETs. IETE Journal of Research, 2022, 68, 2231-2237.	2.6	1
2	A Junctionless Accumulation Mode NC-FinFET Gate Underlap Design for Improved Stability and Self-Heating Reduction. IEEE Transactions on Electron Devices, 2020, 67, 3424-3430.	3.0	12
3	Single Event Transients in Sub-10nm SOI MuGFETs Due to Heavy-Ion Irradiation. IEEE Transactions on Device and Materials Reliability, 2020, 20, 395-403.	2.0	8
4	Impact of Gamma-Ray Radiation on DC and RF Performance of 10-nm Bulk N-Channel FinFETs. IEEE Transactions on Device and Materials Reliability, 2020, 20, 760-766.	2.0	7
5	Experimental Evaluation of Self-Heating and Analog/RF FOM in GAA-Nanowire FETs. IEEE Transactions on Electron Devices, 2019, 66, 3279-3285.	3.0	14
6	Effect of Post Radiation Annealing on the TID Response of 0.18 μ m bulk NFETs. , 2019, , .		4
7	An investigation of reliability and variability issues in nanoscale SOI and multi-gate MOSFETs: modelling, simulation and characterization. CSI Transactions on ICT, 2019, 7, 209-214.	1.0	1
8	SEU Sensitivity of a 14-nm SOI FinFET eDRAM Cell under Heavy-ion Irradiation. , 2018, , .		1
9	Transient Response of 0.18 μ m SOI MOSFETs and SRAM Bit-Cells to Heavy-Ion Irradiation for Variable SOI Film Thickness. IEEE Transactions on Electron Devices, 2018, 65, 4826-4833.	3.0	11
10	Evaluation of 10-nm Bulk FinFET RF Performance—Conventional Versus NC-FinFET. IEEE Electron Device Letters, 2018, 39, 1246-1249.	3.9	49
11	Impact of SOI thickness scaling on alpha-particle irradiation performance of MOSFETs. , 2017, , .		1
12	7-nm Nanowire FET process variation modeling using industry standard BSIM-CMG model. , 2016, , .		6